

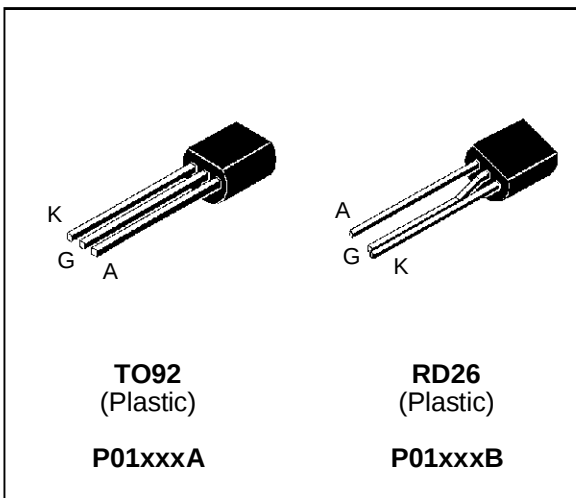
SENSITIVE GATE SCR

FEATURES

- $I_{T(RMS)} = 0.8A$
- $V_{DRM} = 100V$ to $400V$
- Low $I_{GT} < 1\mu A$ max to $< 200\mu A$

DESCRIPTION

The P01xxxA/B series of SCRs uses a high performance planar PNP technology. These parts are intended for general purpose applications where low gate sensitivity is required.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	$T_I = 55^\circ C$	0.8	A
$I_{T(AV)}$	Mean on-state current (180° conduction angle)	$T_I = 55^\circ C$	0.5	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	8	A
		$t_p = 10$ ms	7	
I_t^2	I_t^2 Value for fusing	$t_p = 10$ ms	0.24	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 10$ mA $di_G/dt = 0.1$ A/ μs .		30	A/ μs
T_{stg} T_j	Storage and operating junction temperature range		- 40, + 150 - 40, + 125	$^\circ C$
T_I	Maximum lead temperature for soldering during 10s at 2mm from case		260	$^\circ C$

Symbol	Parameter	Voltage				Unit
		A	B	C	D	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$ $R_{GK} = 1K\Omega$	100	200	300	400	V

P01xxxA/B

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	150	°C/W
Rth(j-l)	Junction to leads for DC	80	°C/W

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 0.1 W P_{GM} = 2 W (tp = 20 μ s) I_{GM} = 1 A (tp = 20 μ s)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Sensitivity					Unit
				02	09	11	15	18	
I_{GT}	$V_D=12V$ (DC) $R_L=140\Omega$	$T_j=25^\circ C$	MIN			4	15	0.5	μA
			MAX	200	1	25	50	5	
V_{GT}	$V_D=12V$ (DC) $R_L=140\Omega$	$T_j=25^\circ C$	MAX	0.8					V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3k\Omega$ $R_{GK}=1K\Omega$	$T_j=125^\circ C$	MIN	0.1					V
V_{RGM}	$I_{RG}=10\mu A$	$T_j=25^\circ C$	MIN	8					V
tg d	$V_D=V_{DRM}$ $I_{TM}=3 \times I_{T(AV)}$ $dI_G/dt=0.1A/\mu s$ $I_G=10mA$	$T_j=25^\circ C$	TYP	0.5					μs
I_H	$I_T=50mA$ $R_{GK}=1K\Omega$	$T_j=25^\circ C$	MAX	5					mA
I_L	$I_G=1mA$ $R_{GK}=1K\Omega$	$T_j=25^\circ C$	MAX	6					mA
V_{TM}	$I_{TM}=1.6A$ tp = 380 μs	$T_j=25^\circ C$	MAX	1.93					V
I_{DRM} I_{RRM}	$V_D=V_{DRM}$ $R_{GK}=1K\Omega$ $V_R=V_{RRM}$	$T_j=25^\circ C$	MAX	1					μA
		$T_j=125^\circ C$	MAX	100					μA
dV/dt	$V_D=67\%V_{DRM}$ $R_{GK}=1K\Omega$	$T_j=125^\circ C$	MIN	25	25	50	100	30	V/ μs
tq	$I_{TM}=3 \times I_{T(AV)}$ $V_R=35V$ $dI/dt=10A/\mu s$ tp = 100 μs $dV/dt=10V/\mu s$ $V_D=67\%V_{DRM}$ $R_{GK}=1K\Omega$	$T_j=125^\circ C$	MAX	200					μs

ORDERING INFORMATION

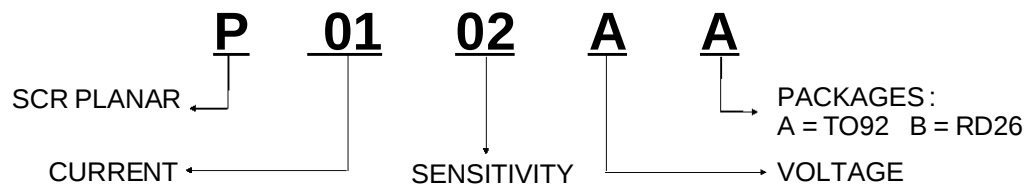


Fig.1 : Maximum average power dissipation versus average on-state current.

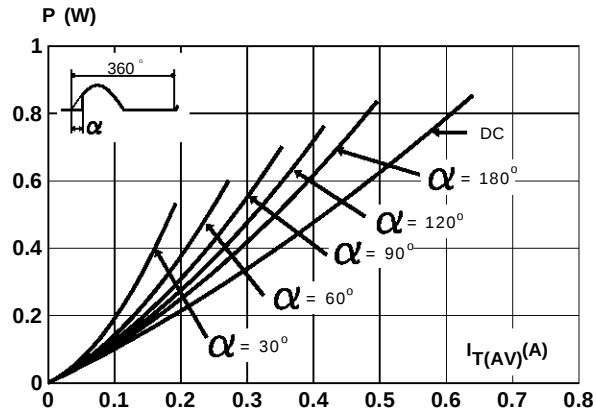


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (T_{amb} and T_{lead}).

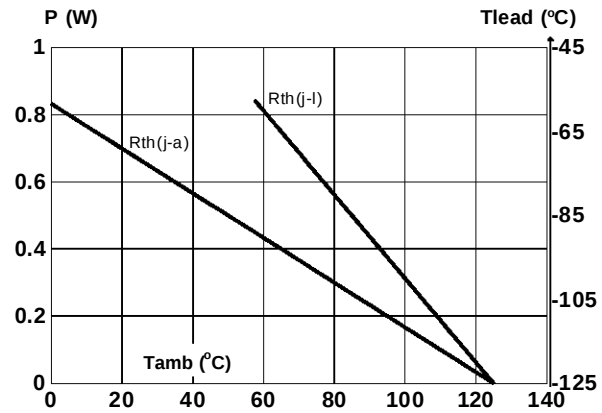


Fig.3 : Average on-state current versus lead temperature.

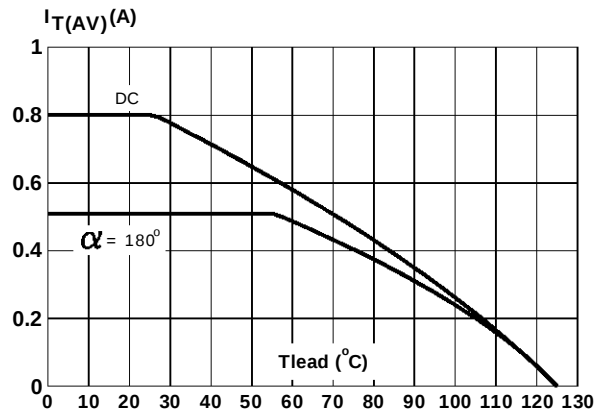


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

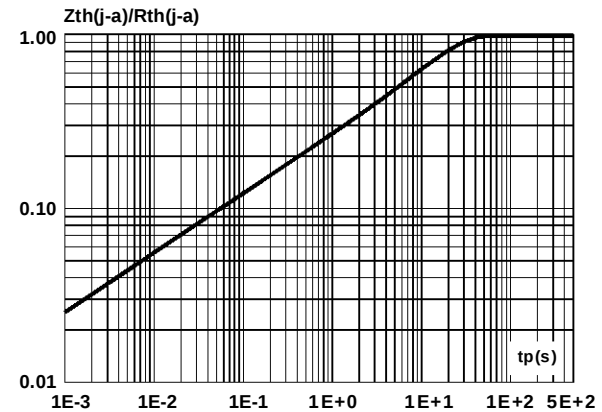


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

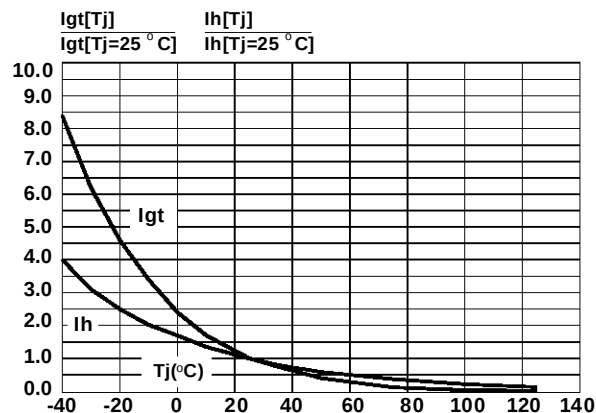


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

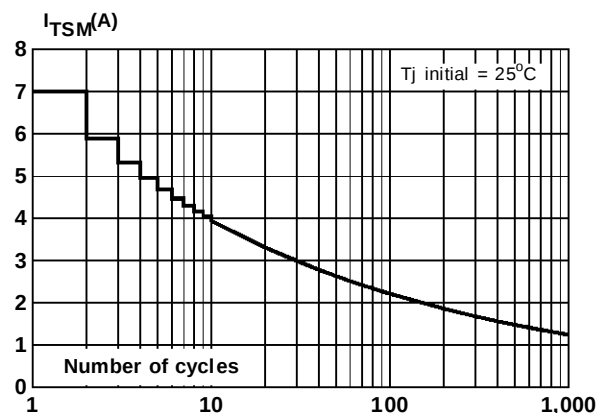


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

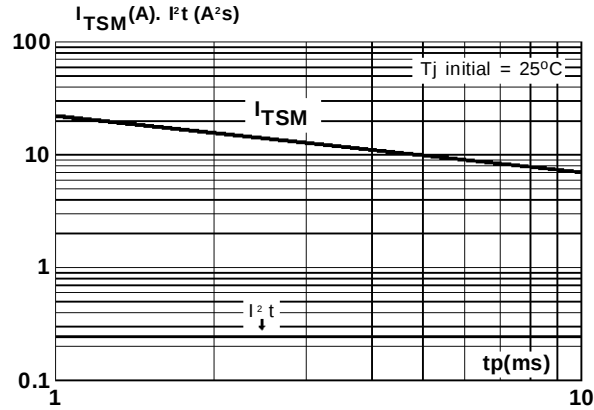


Fig.8 : On-state characteristics (maximum values).

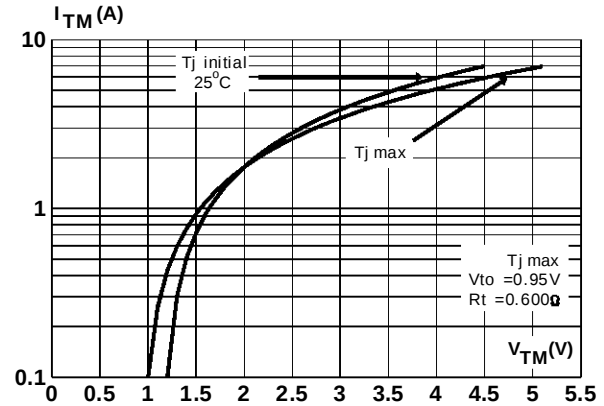
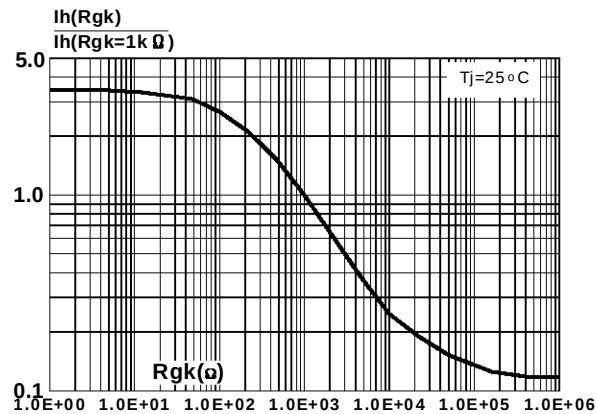


Fig.9 : Relative variation of holding current versus gate-cathode resistance (typical values).



PACKAGE MECHANICAL DATA

TO92 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	1.35			0.053		
B			4.7			0.185
C	2.54			0.100		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			3.7			0.146
a			0.45			0.017

Marking : type number

Weight : 0.2 g

PACKAGE MECHANICAL DATA

RD26 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	2.54			0.100		
B			3.7			0.146
C	1.35			0.053		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			4.7			0.185
G			3.0			0.118
a			0.45			0.177

Marking : type number

Weight : 0.2 g

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1995 SGS-THOMSON Microelectronics - All rights reserved.

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.